





TS13003

High Voltage NPN Transistor

<div style="display: flex; justify-content: space-around;"> <div style="text-align: center;"> <p>TO-126</p>  <p>1 2 3</p> </div> <div style="text-align: center;"> <p>TO-92</p>  <p>1 2 3</p> </div> </div> <p style="margin-top: 10px;">Pin assignment: 1. Emitter 2. Collector 3. Emitter</p>	<p>$BV_{CEO} = 400V$ $BV_{CBO} = 700V$ $I_C = 1.5A$ $V_{CE(SAT)} = 0.8V @ I_C / I_B = 0.5A / 0.1A$</p>
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<p>Features</p> <ul style="list-style-type: none"> ◇ High voltage. ◇ High speed switching <p>Structure</p> <ul style="list-style-type: none"> ◇ Silicon triple diffused type. ◇ NPN silicon transistor 	<p>Ordering Information</p> <table border="1" style="width: 100%; border-collapse: collapse; text-align: center;"> <thead> <tr> <th>Part No.</th> <th>Packing</th> <th>Package</th> </tr> </thead> <tbody> <tr> <td>TS13003CT</td> <td rowspan="2">Bulk</td> <td>TO-92</td> </tr> <tr> <td>TS13003CK</td> <td>TO-126</td> </tr> </tbody> </table>	Part No.	Packing	Package	TS13003CT	Bulk	TO-92	TS13003CK	TO-126
Part No.	Packing	Package							
TS13003CT	Bulk	TO-92							
TS13003CK		TO-126							

Absolute Maximum Rating ($T_a = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	700V	V
Collector-Emitter Voltage	V_{CEO}	400V	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	DC	I_C	A
	Pulse		
Collector Power Dissipation	TO-92	P_D	W
	TO-126		
Operating Junction Temperature	T_J	+150	$^\circ C$
Operating Junction and Storage Temperature Range	T_{STG}	- 55 to +150	$^\circ C$

Note: 1. Single pulse, $P_w = 5mS$, Duty $\leq 10\%$

Electrical Characteristics

$T_a = 25^\circ C$ unless otherwise noted

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Collector-Base Voltage	$I_C = 5mA, I_B = 0$	BV_{CBO}	700			V
Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_E = 0$	BV_{CEO}	400			V
Emitter-Base Breakdown Voltage	$I_E = 1mA, I_C = 0$	BV_{EBO}	9			V
Collector Cutoff Current	$V_{CB} = 700V, I_E = 0$	I_{CBO}			100	μA
Emitter Cutoff Current	$V_{EB} = 9V, I_C = 0$	I_{EBO}			10	μA
Collector-Emitter Saturation Voltage	$I_C / I_B = 1.5A / 0.5A$	$V_{CE(SAT)1}$			3	V
	$I_C / I_B = 0.5A / 0.1A$	$V_{CE(SAT)2}$			0.5	
DC Current Gain	$V_{CE} = 2V, I_C = 0.5A$	h_{FE}	8		40	
Frequency	$V_{CE} = 10V, I_C = 0.1A$	f_T	4			MHz
Output Capacitance	$V_{CB} = 10V, f = 0.1MHz$	Cob		21		pF
Turn On Time	$V_{CC} = 125V, I_C = 1A,$ $I_{B1} = 0.2A, I_{B2} = - 0.2A,$ $R_L = 125ohm$	t_{ON}		1.1		μS
Storage Time		t_{STG}			4	μS
Fall Time		t_f				0.7

Note : pulse test: pulse width $\leq 5mS$, duty cycle $\leq 10\%$

Electrical Characteristics Curve

Figure 1. Static Characteristic

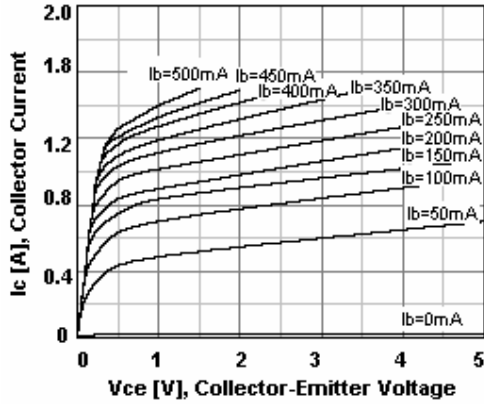


Figure 2. DC Current Gain

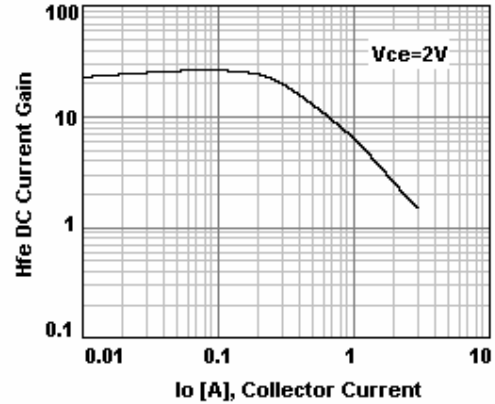


Figure 3. Vce(sat) v.s. Vbe(sat)

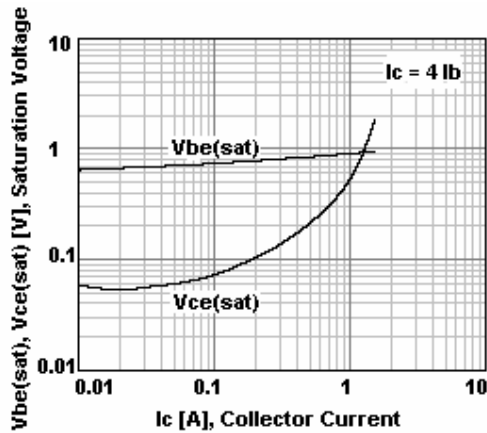


Figure 4. Switching Time

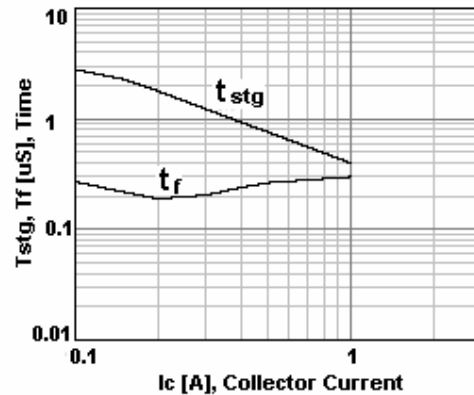


Figure 5. Safe Operating Area

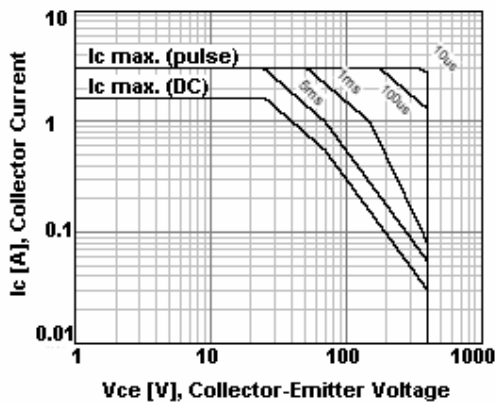
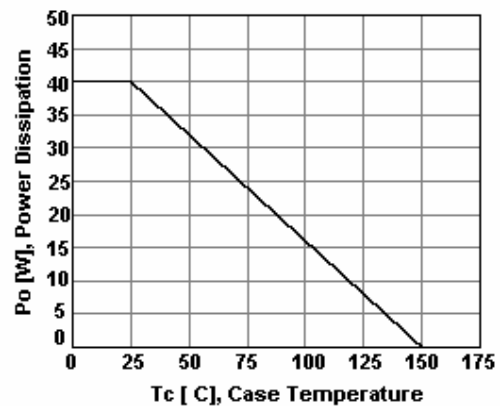
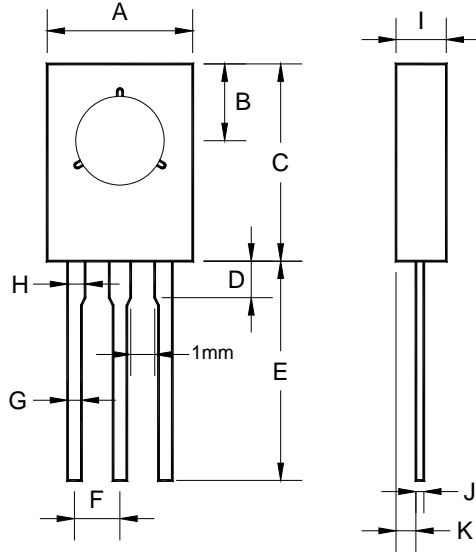


Figure 6. Power Derating

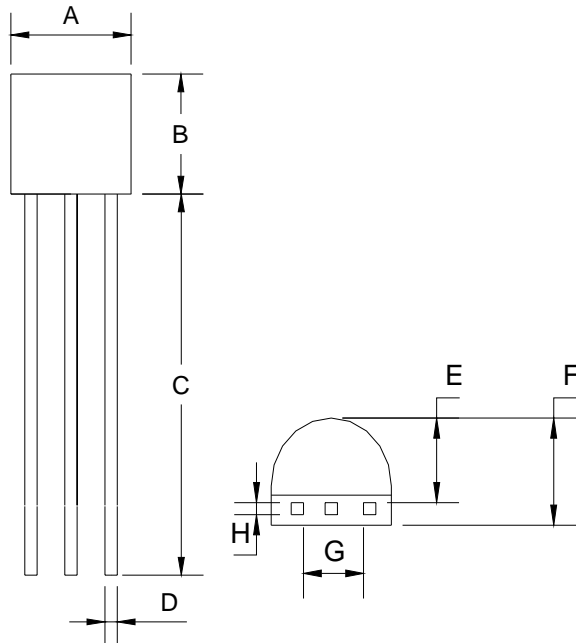


TO-126 Mechanical Drawing



TO-126 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.00 (typ)		0.315(typ)	
B	4.20 (typ)		0.165 (typ)	
C	10.58	11.00	0.417	0.433
D	2.00 (typ)		0.079 (typ)	
E	12.00(typ)		0.472(typ)	
F	2.50(typ)		0.098 (typ)	
G	0.74	0.78	0.029	0.031
H	0.8 (typ)		0.031(typ)	
I	2.56	3.00	0.101	0.118
J	0.38	0.50	0.015	0.020
K	1.1 (typ)		0.043 (typ)	

TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017